

2N6674 Transistors

Si NPN Power BJT

Military/High-Rel N

$V_{(BR)CEO}$ (V) 300

$V_{(BR)CBO}$ (V) 450

I_C Max. (A) 15

Absolute Max. Power Diss. (W) 175

Maximum Operating Temp (θC) 175 \circ

I_{CBO} Max. (A) 100 μA

@ V_{CBO} (V) (Test Condition)

V_{CEsat} Max. (V)

@ I_C (A) (Test Condition)

@ I_B (A) (Test Condition)

h_{FE} Min. Current gain. 8.0

h_{FE} Max. Current gain. 20

@ I_C (A) (Test Condition) 10

@ V_{CE} (V) (Test Condition) 5.0

f_T Min. (Hz) Transition Freq 15M

@ I_C (A) (Test Condition)

@ V_{CE} (V) (Test Condition)

t_d Max. (s) Delay time. 100n

t_r Max. (s) Rise time 600n

t_{on} Max. (s) On time.

Datasheet.Directory